



SLPS362A - SEPTEMBER 2012 - REVISED JANUARY 2013

60-V, N-Channel NexFET[™] Power MOSFETs

Check for Samples: CSD18533KCS

FEATURES

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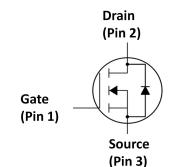
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- TO-220 Plastic Package

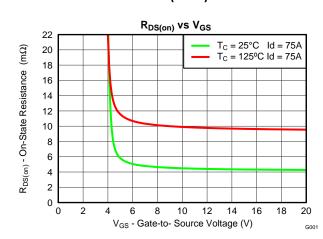
APPLICATIONS

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Motor Control

DESCRIPTION

The NexFET[™] power MOSFET has been designed to minimize losses in power conversion applications.





PRODUCT SUMMARY

$T_A = 25^{\circ}$	С	TYPICAL VA	UNIT	
V _{DS}	Drain to Source Voltage	60		V
Qg	Gate Charge Total (10V)	28		nC
Q _{gd}	Gate Charge Gate to Drain	3.9		nC
Р	Drain to Source On Resistance	V _{GS} = 4.5V 6.9		mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V 5		mΩ
V _{GS(th)}	Threshold Voltage	1.9		V

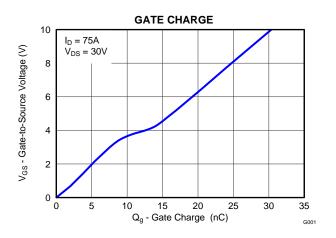
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD18533KCS	TO-220 Plastic Package	Tube	50	Tube

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C	VALUE	UNIT				
V _{DS}	Drain to Source Voltage	60	V				
V _{GS}	Gate to Source Voltage	±20	V				
	Continuous Drain Current (Package limited), $T_{C} = 25^{\circ}C$	100					
I _D	Continuous Drain Current (Silicon limited), $T_{C} = 25^{\circ}C$	114	A				
	Continuous Drain Current (Silicon limited), $T_{C} = 100^{\circ}C$	72					
I _{DM}	Pulsed Drain Current ⁽¹⁾	135	А				
PD	Power Dissipation	160	W				
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C				
E _{AS}	Avalanche Energy, single pulse $I_D = 52A$, L = 0.1mH, $R_G = 25\Omega$	135	mJ				

(1) Pulse duration \leq 300µs, duty cycle \leq 2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
Static Cl	haracteristics				
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	60		V
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 48V$		1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = 20V$		100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.5 1.9	2.3	V
		V _{GS} = 4.5V, I _D = 75A	6.9	9.0	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V, I _D = 75A	5.0	6.3	mΩ
9 _{fs}	Transconductance	V _{DS} = 30V, I _D = 75A	150		S
Dynamic	Characteristics				
C _{iss}	Input Capacitance		2420	3025	pF
C _{oss}	Output Capacitance	V _{GS} = 0V, V _{DS} = 30V, f = 1MHz	300	375	pF
C _{rss}	Reverse Transfer Capacitance		7	9.1	pF
R _G	Series Gate Resistance		1.4	2.8	Ω
Qg	Gate Charge Total (4.5V)		14	17	nC
Qg	Gate Charge Total (10V)		28	34	nC
Q _{gd}	Gate Charge Gate to Drain	V _{DS} = 30V, I _D = 75A	3.9		nC
Q _{gs}	Gate Charge Gate to Source		9.4		nC
Q _{g(th)}	Gate Charge at Vth		4.6		nC
Q _{oss}	Output Charge	$V_{DS} = 30V, V_{GS} = 0V$	31		nC
t _{d(on)}	Turn On Delay Time		5.7		ns
t _r	Rise Time	V _{DS} = 30V, V _{GS} = 10V,	4.8		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 75A, R_G = 0\Omega$	13		ns
t _f	Fall Time		3.2		ns
Diode Cl	haracteristics			ľ	
V _{SD}	Diode Forward Voltage	I _{SD} = 75A, V _{GS} = 0V	0.8	1	V
Q _{rr}	Reverse Recovery Charge	$V_{DS} = 30V, I_{F} = 75A,$	97		nC
t _{rr}	Reverse Recovery Time	di/dt = 300A/µs	49		ns

THERMAL CHARACTERISTICS

($T_A = 25^{\circ}C$ unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{ extsf{ heta}JC}$	Thermal Resistance Junction to Case			0.8	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient			62	°C/W

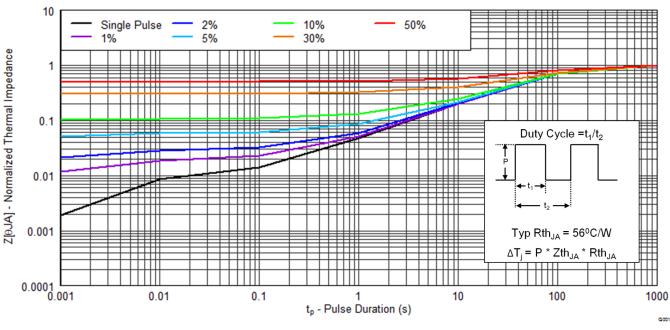


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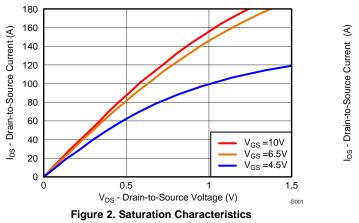
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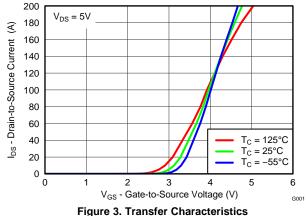
TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





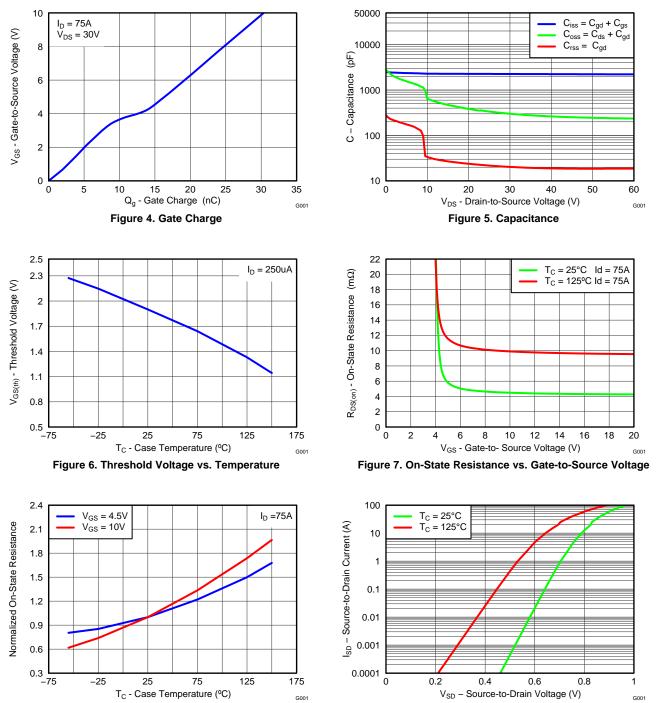




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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



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Figure 8. Normalized On-State Resistance vs. Temperature

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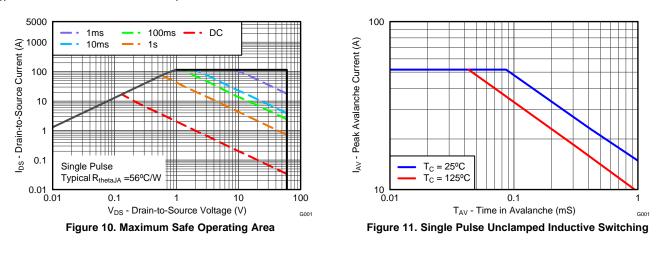


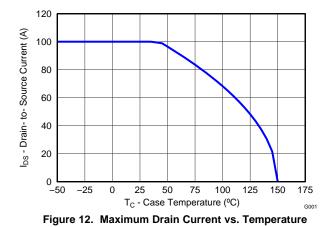
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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



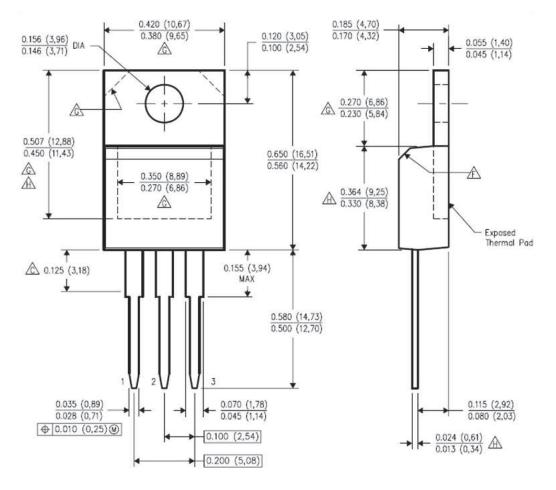


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MECHANICAL DATA

KCS Package Dimensions



Notes:

- 1. All linear dimensions are in inches
- 2. This drawing is subject to change without notice
- 3. Lead Dimensions are not controlled within "C" area
- 4. All lead dimensions apply before solder dip
- 5. The center lead is in electrical contact with the mounting tab
- 6. The chamfer at "F" is optional
- 7. Thermal pad contour at "G" optional with these dimensions
- 8. "H" Falls within JEDEC TO-220 variation AB, except minimum lead thickness, minimum exposed pad length, and maximum body length.

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Position	Designation
Pin 1	Gate
Pin 2 / Tab	Drain
Pin 3	Source

Table 1. Pin Configuration

CSD18533KCS

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REVISION HISTORY

Changes from Original (September 2012) to Revision A

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Samples
	(1)		Drawing			(2)		(3)	(Requires Login)
CSD18533KCS	ACTIVE	TO-220	KCS	3	50	Pb-Free (RoHS Exempt)	CU SN	N / A for Pkg Type	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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